

isc N-Channel MOSFET Transistor

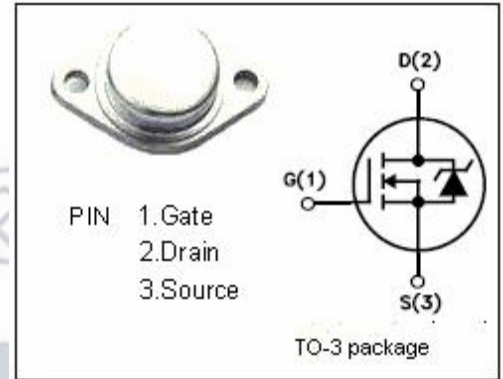
4N45

DESCRIPTION

- Drain Current $I_D = 4A @ T_C = 25^\circ C$
- Drain Source Voltage-
: $V_{DSS} = 450V(\text{Min})$
- Fast Switching Speed

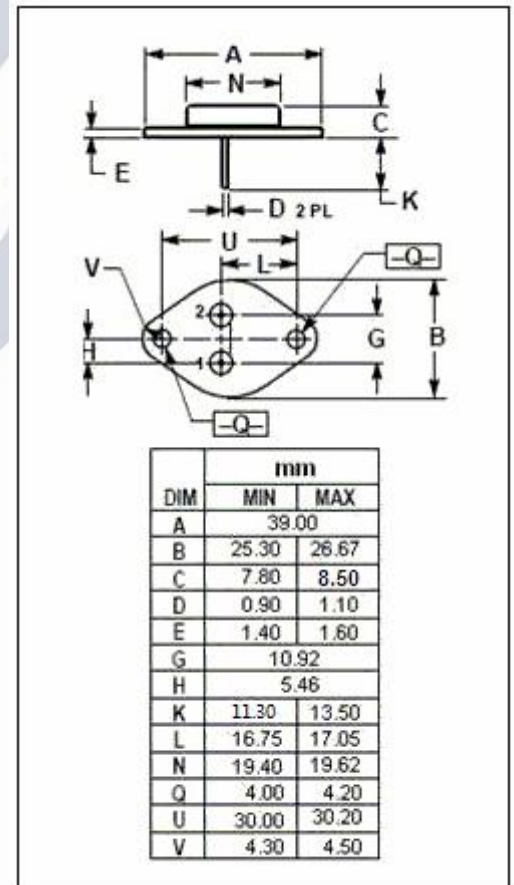
APPLICATIONS

- General purpose power amplifier



ABSOLUTE MAXIMUM RATINGS($T_C = 25^\circ C$)

SYMBOL	PARAMETER	VALUE	UNIT
V_{DSS}	Drain-Source Voltage ($V_{GS} = 0$)	450	V
V_{GS}	Gate-Source Voltage	± 20	V
I_D	Drain Current-continuous@ $T_C = 25^\circ C$	4	A
$I_{D(puls)}$	Pulse Drain Current	10	A
P_{tot}	Total Dissipation@ $T_C = 25^\circ C$	100	W
T_j	Max. Operating Junction Temperature	150	$^\circ C$
T_{stg}	Storage Temperature Range	-55~150	$^\circ C$



• THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
$R_{th\ j-c}$	Thermal Resistance, Junction to Case	1.67	$^\circ C/W$
$R_{th\ j-a}$	Thermal Resistance, Junction to Ambient	62.5	$^\circ C/W$

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• ELECTRICAL CHARACTERISTICS (T_c=25°C)

SYMBOL	PARAMETER	CONDITIONS	MIN	TYPE	MAX	UNIT
V _{(BR)DSS}	Drain-Source Breakdown Voltage	V _{GS} = 0; I _D = 250μA	450			V
V _{GS(th)}	Gate Threshold Voltage	V _{DS} = V _{GS} ; I _D =250μA	2.0		4.0	V
V _{SD}	Diode Forward On-Voltage	I _S =4A; V _{GS} = 0			1.4	V
R _{DS(on)}	Drain-Source On-Resistance	V _{GS} = 10V; I _D =2.5A			2.5	Ω
I _{GSS}	Gate-Body Leakage Current	V _{GS} = ±20V; V _{DS} = 0			±100	nA
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} = 450V; V _{GS} = 0			10	μA